

Si3861DV

Integrated Load Switch

General Description

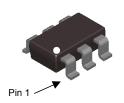
This device is particularly suited for compact power management in portable electronic equipment where 2.5V to 8V input and 2.8A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large P-Channel power MOSFET (Q2) in one tiny SuperSOTTM-6 package.

Applications

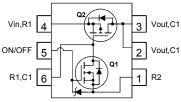
- Load switch
- · Power management

Features

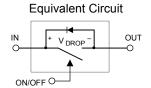
- -2.8 A, -8 V. $R_{DS(ON)} = 55 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 70 \text{ m}\Omega$ @ $V_{GS} = -2.5 \text{ V}$ $R_{DS(ON)} = 100 \text{ m}\Omega$ @ $V_{GS} = -1.8 \text{ V}$
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>6KV Human body model)
- High performance trench technology for extremely low $R_{\mathsf{DS}(\mathsf{ON})}$







See Application Circuit



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{IN}	Maximum Input Voltage		± 8	V
V _{ON/OFF}	High level ON/OFF voltage range		-0.5 to 8	V
I _{Load}	Load Current - Continuous	(Note 1)	-2.8	A
	– Pulsed		– 9	
P _D	Maximum Power Dissipation	(Note 1)	0.7	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	180	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Package Marking and Ordering Information

Device Marking	Device Marking Device Reel Size		Tape width	Quantity	
.861	Si3861DV	7"	8mm	3000 units	

Electrical Characteristics T_A = 25°C unless otherwise noted Тур Symbol Parameter **Test Conditions** Min Max Units **Off Characteristics** Vin Breakdown Voltage $V_{ON/OFF} = 0 \text{ V}, I_D = -250 \mu\text{A}$ 8 ٧ Zero Gate Voltage Drain Current $V_{IN} = 6.4 V$ $V_{ON/OFF} = 0 V$ -1 μΑ I_{Load} $V_{ON/OFF} = 0 V$, $V_{IN} = 8 V$ -100 Leakage Current, Forward nΑ I_{FL} $V_{ON/OFF} = \overline{0 V}$ I_{RL} Leakage Current, Reverse $V_{IN} = -8 \text{ V}$ 100 nΑ On Characteristics (Note 2) V_{ON/OFF (th)} Gate Threshold Voltage $V_{IN} = V_{ON/OFF}$, $I_D = -250 \mu A$ 0.4 0.9 1.5 ٧ $R_{\text{DS(on)}}$ Static Drain-Source $V_{IN} = 4.5 \text{ V}, \qquad I_D = -2.8 \text{A}$ 34 55 $\mathsf{m}\Omega$ $V_{IN} = 2.5 V,$ On-Resistance (Q2) $I_D = -2.5 A$ 45 70 $V_{IN} = 1.8 V,$ $I_D = -2.0 A$ 64 100 R_{DS(on)} $I_{D} = 0.4A$ Static Drain-Source $V_{IN} = 4.5 V,$ 3.1 4 Ω $V_{IN} = 2.7 \text{ V},$ 5 On-Resistance (Q1) $I_D = 0.2 A$ 3.8

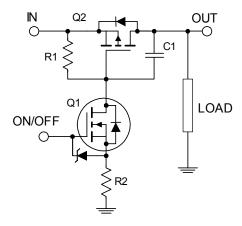
Drain-Source Diode Characteristics and Maximum Ratings

Is	Maximum Continuous Drain–Source Diode Forward Current			-0.6	Α
V_{SD}	Drain–Source Diode Forward Voltage	$V_{ON/OFF} = 0 \text{ V}, I_S = -0.6 \text{ A} \text{ (Note 2)}$		-1.2	V

Notes

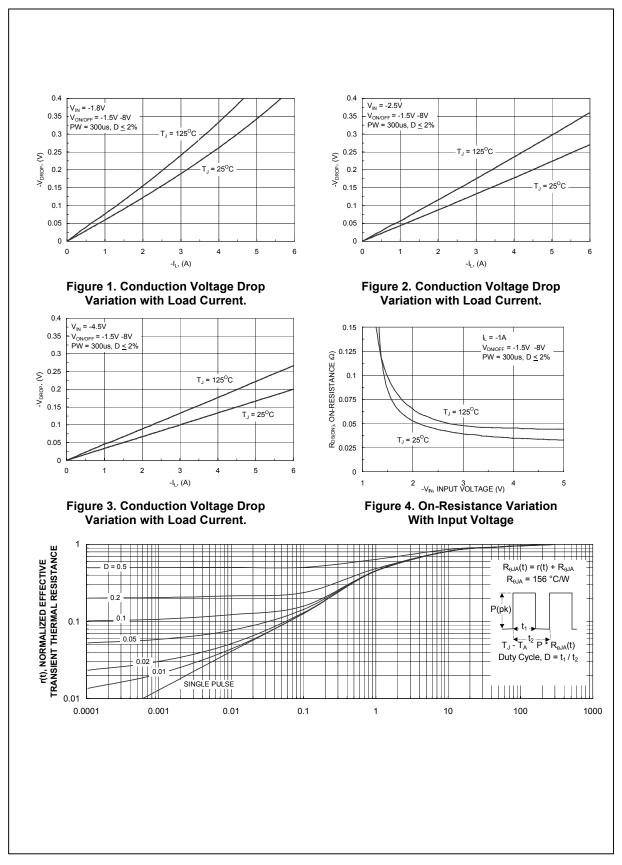
- 1. R BLA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R BJC is guaranteed by design while R BJA is determined by the user's board design.
- 2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%.

Si3861DV Load Switch Application Circuit



External Component Recommendation:

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030.



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